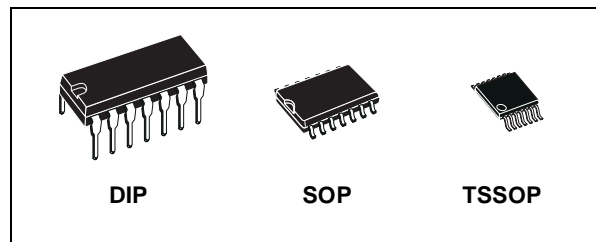




# M74HC242

## QUAD BUS TRANSCEIVER (3 - STATE)

- HIGH SPEED:  
 $t_{PD} = 11\text{ns}$  (TYP.) at  $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu\text{A}$ (MAX.) at  $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\%$   $V_{CC}$  (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 6\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH  
 74 SERIES 242



### ORDER CODES

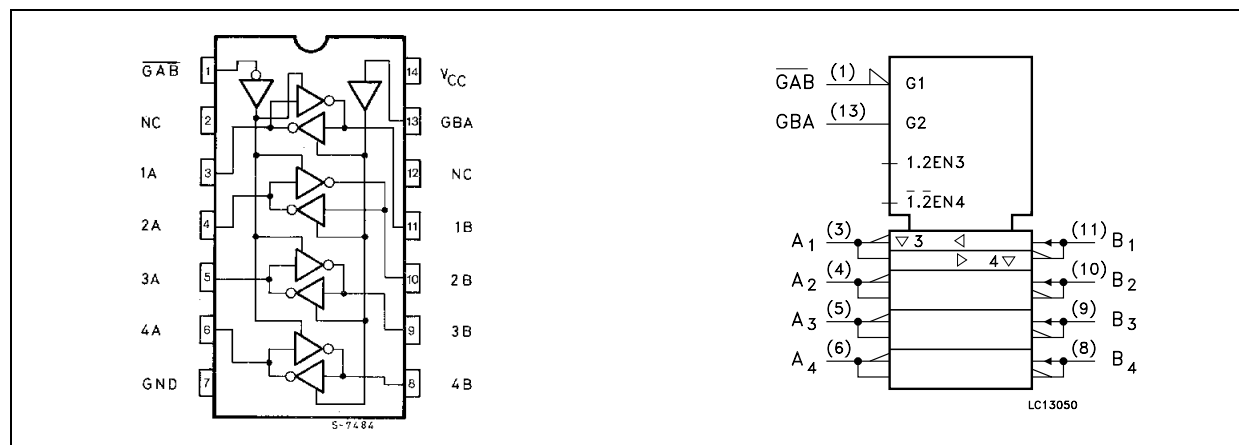
PACKAGE	TUBE	T & R
DIP	M74HC242B1R	
SOP	M74HC242M1R	M74HC242RM13TR
TSSOP		M74HC242TTR

### DESCRIPTION

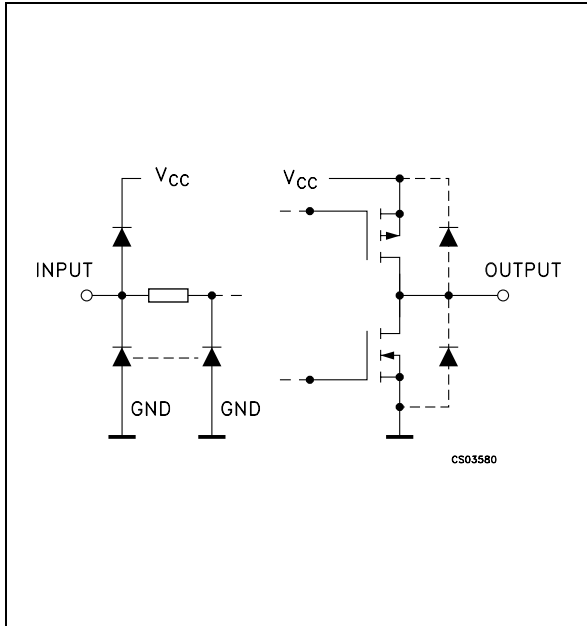
The M74HC242 is an high speed CMOS QUAD BUS TRANSCEIVER (3-STATE) fabricated with silicon gate C<sup>2</sup>MOS technology. The M74HC242 is a 3-state bidirectional inverting buffer and is intended for two way asynchronous communication between data buses. It has high drive current outputs which enable high speed

operation when driving large bus capacitance. The device has one active high enable (GBA), and one active low enable (GAB). All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



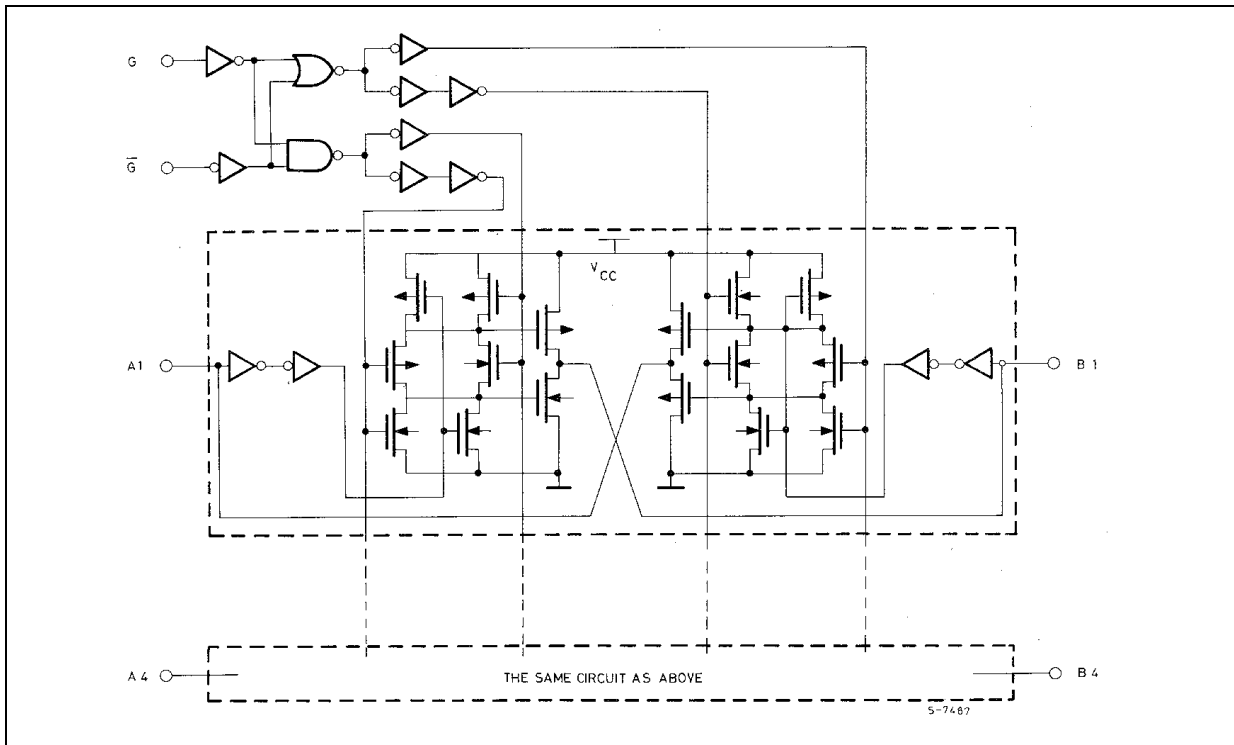
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	$\overline{\text{GAB}}$	Output Enable Input (Active LOW)
2, 12	NC	Not Connected
3, 4, 5, 6	1A to 4A	Data Inputs/Outputs
11, 10, 9, 8	1B to 4B	Data Inputs/Outputs
13	GBA	Output Enable Input
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

TRUTH TABLE

INPUTS		FUNCTION		OUTPUTS
$\overline{\text{GAB}}$	GBA	A BUS	B BUS	
H	H	OUTPUT	INPUT	$A = \overline{B}$
L	L	INPUT	OUTPUT	$B = \overline{A}$
H	L	HIGH IMPEDANCE		Z
L	H	HIGH IMPEDANCE		Z

LOGIC DIAGRAM



This logic diagram has not been used to estimate propagation delays

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 35$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 70$	mA
$P_D$	Power Dissipation	500(*)	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply Voltage	2 to 6	V	
$V_I$	Input Voltage	0 to $V_{CC}$	V	
$V_O$	Output Voltage	0 to $V_{CC}$	V	
$T_{op}$	Operating Temperature	-55 to 125	°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I <sub>O</sub> =-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-7.8 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =7.8 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			± 0.5		± 5		± 10	μA
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			4		40		80	μA

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50$  pF, Input  $t_r = t_f = 6$  ns)

Symbol	Parameter	Test Condition		Value						Unit		
		$V_{CC}$ (V)	$C_L$ (pF)	$T_A = 25^\circ\text{C}$			$-40$ to $85^\circ\text{C}$		$-55$ to $125^\circ\text{C}$			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
$t_{TLH}$ $t_{THL}$	Output Transition Time	2.0	50		25	60		75		90	ns	
		4.5			7	12		15		18		
		6.0			6	10		13		15		
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time	2.0	50		39	90		115		135	ns	
		4.5			13	18		23		27		
		6.0			11	15		20		23		
		2.0	150		51	145		180		220	ns	
		4.5			17	29		36		44		
		6.0			14	25		31		37		
$t_{PZL}$ $t_{PZH}$	High Impedance Output Enable Time	2.0	50	$R_L = 1\text{ K}\Omega$		57	145		180		220	ns
		4.5				18	29		36		44	
		6.0				15	25		31		37	
		2.0	150	$R_L = 1\text{ K}\Omega$		70	175		220		265	ns
		4.5				22	35		44		53	
		6.0				19	30		37		45	
$t_{PLZ}$ $t_{PHZ}$	High Impedance Output Disable Time	2.0	50	$R_L = 1\text{ K}\Omega$		45	150		190		225	ns
		4.5				20	30		38		45	
		6.0				17	26		32		38	

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40$ to $85^\circ\text{C}$		$-55$ to $125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance	5.0			5	10		10		10	pF
$C_{PD}$	Power Dissipation Capacitance (note 1)	5.0			30						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

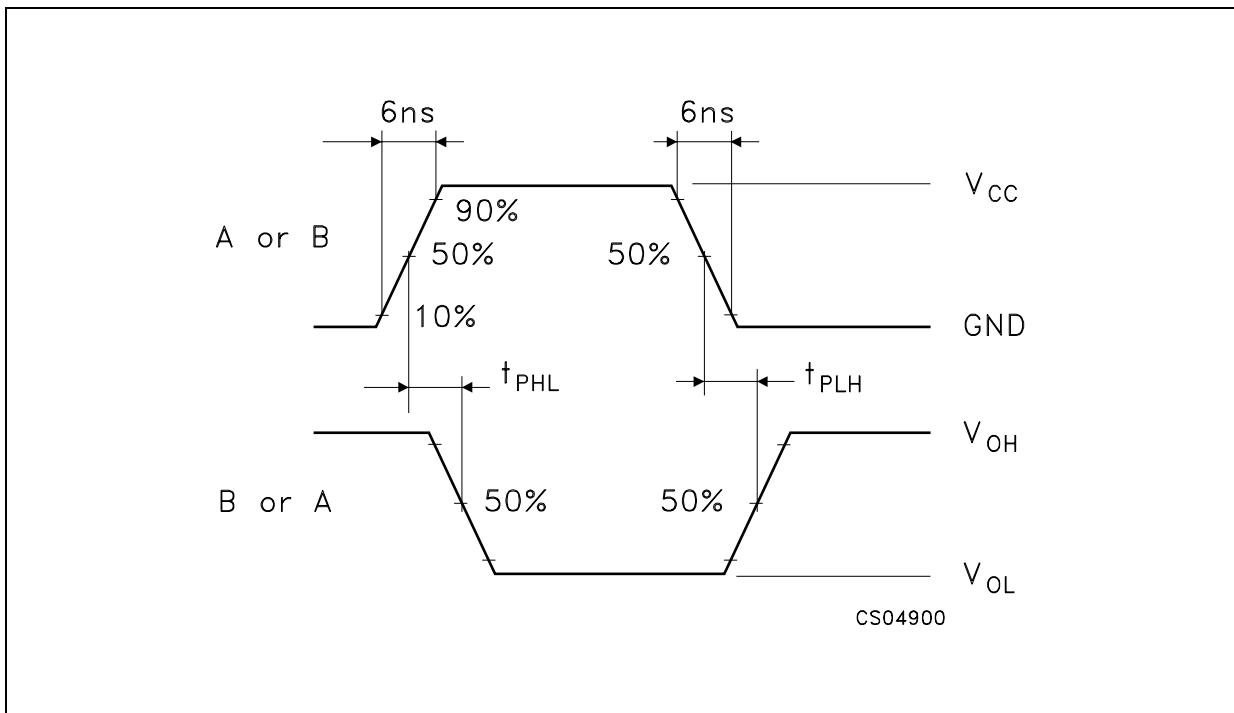
TEST CIRCUIT

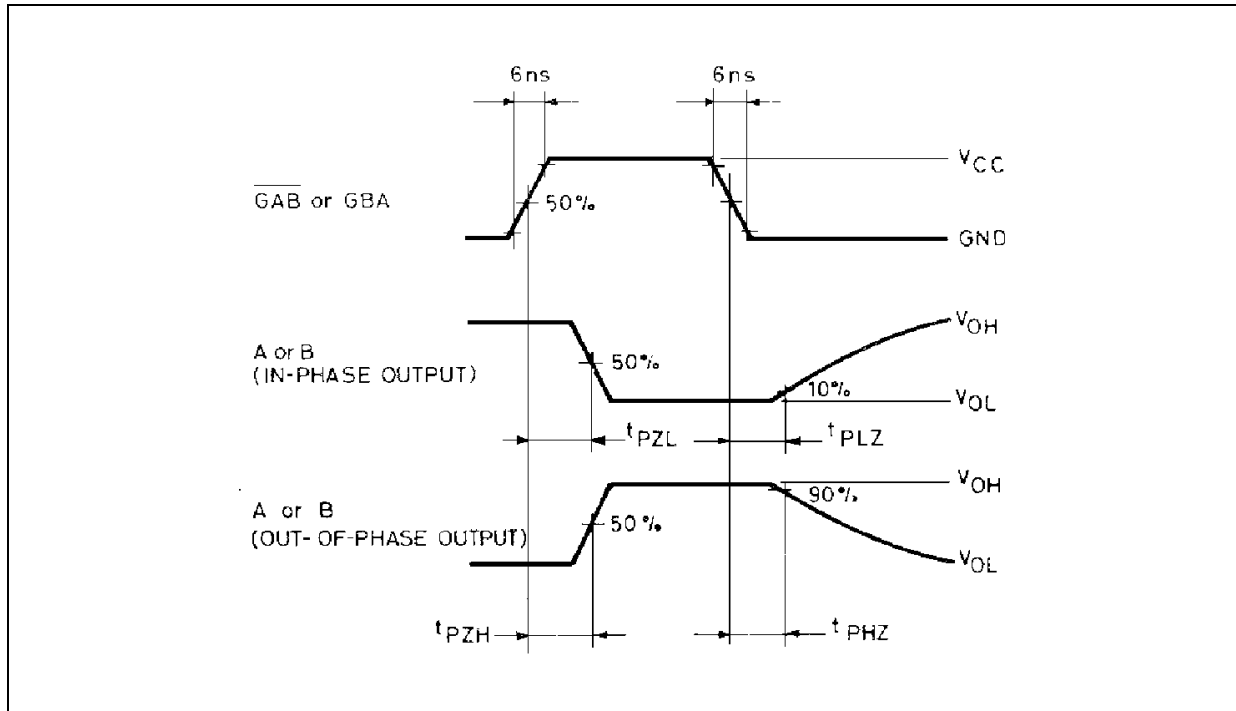


TEST	SWITCH
$t_{PLH}$ , $t_{PHL}$	Open
$t_{PZL}$ , $t_{PLZ}$	$V_{CC}$
$t_{PZH}$ , $t_{PHZ}$	GND

$C_L$  = 50pF/150pF or equivalent (includes jig and probe capacitance)  
 $R_1$  = 1K $\Omega$  or equivalent  
 $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

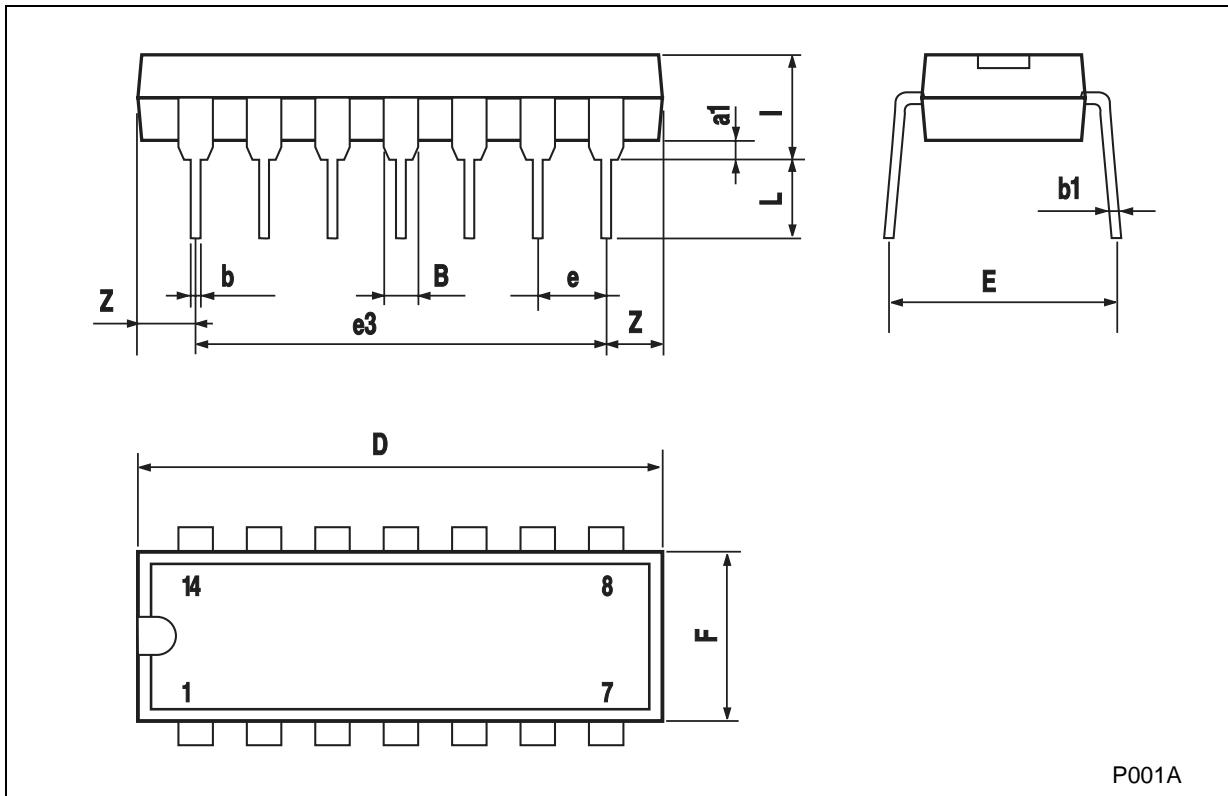
WAVEFORM 1 : PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIME( $f=1\text{MHz}$ ; 50% duty cycle)

**Plastic DIP-14 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A



## SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



**TSSOP14 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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